

LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 8 A
V_{RRM}	40 V
T_j (max)	150 °C
V_F (max)	0.45 V

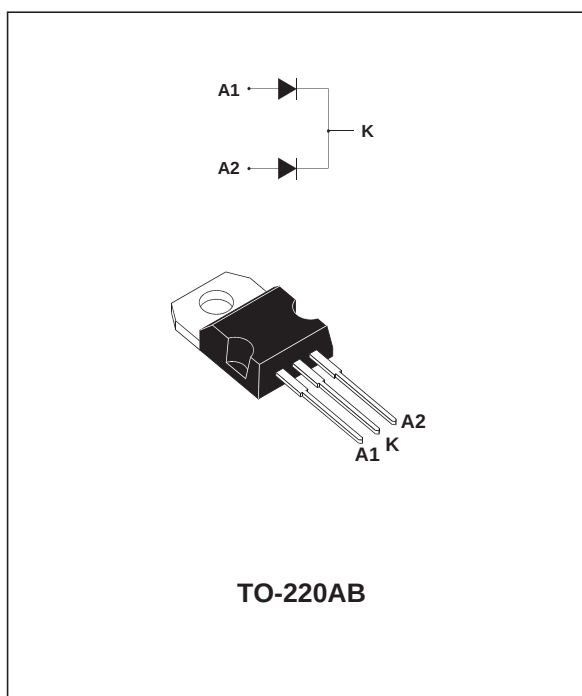
FEATURES AND BENEFITS

- LOW FORWARD VOLTAGE DROP FOR LESS POWER DISSIPATION
- NEGLIGIBLE SWITCHING LOSSES ALLOWING HIGH FREQUENCY OPERATION
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual center tap Schottky barrier rectifier designed for high frequency Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in TO-220AB this device is intended for use in low voltage, high frequency converters, free-wheeling and polarity protection applications.



TO-220AB

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			40	V
I _{F(RMS)}	RMS forward current			30	A
I _{F(AV)}	Average forward current	Tc = 140°C δ = 0.5	Per diode	8	A
			Per device	16	A
I _{FSM}	Surge non repetitive forward current	tp = 10 ms sinusoidal		180	A
I _{RRM}	Repetitive peak reverse current	tp = 2 μs square F=1kHz		1	A
I _{RSM}	Non repetitive peak reverse current	tp = 100 μs square		2	A
P _{ARM}	Repetitive peak avalanche power	tp = 1μs Tj = 25°C		4000	W
T _{stg}	Storage temperature range			- 65 to + 150	°C
Tj	Maximum operating junction temperature *			150	°C
dV/dt	Critical rate of rise of reverse voltage			10000	V/μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

STPS16L40CT

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	2.2	$^{\circ}\text{C/W}$
		Total	1.3	
$R_{th(c)}$		Coupling	0.3	

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			0.7	mA
		$T_j = 100^{\circ}\text{C}$			15	35	mA
V_F^*	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 8\text{ A}$			0.5	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 8\text{ A}$		0.39	0.45	
		$T_j = 25^{\circ}\text{C}$	$I_F = 16\text{ A}$			0.63	
		$T_j = 125^{\circ}\text{C}$	$I_F = 16\text{ A}$		0.55	0.64	

Pulse test : * $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :
 $P = 0.26 \times I_{F(AV)} + 0.024 I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

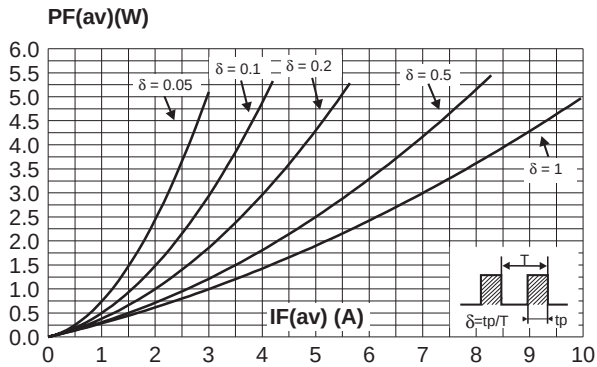


Fig. 3: Normalized avalanche power derating versus pulse duration.

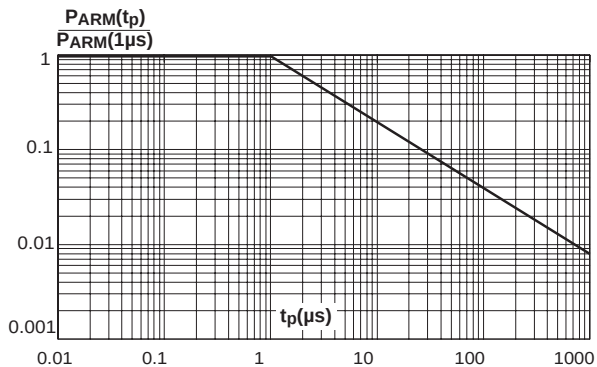


Fig. 2: Average current versus ambient temperature ($\delta = 0.5$) (per diode).

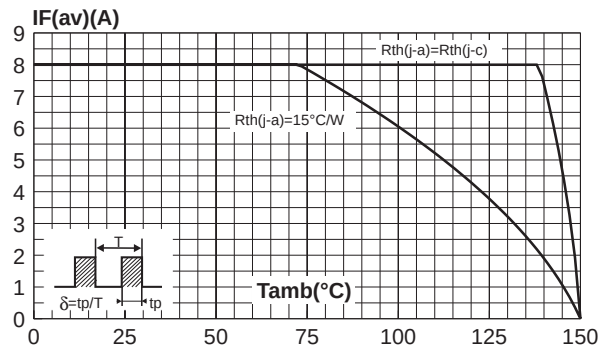


Fig. 4: Normalized avalanche power derating versus junction temperature.

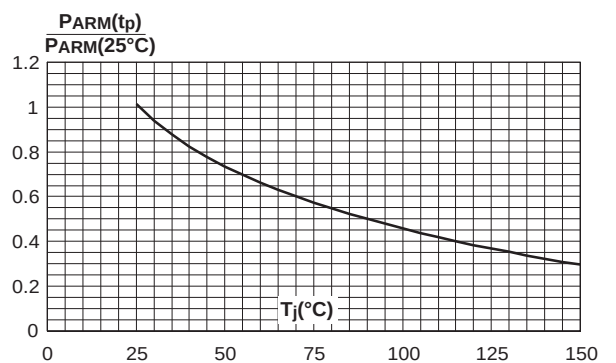


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values) (per diode).

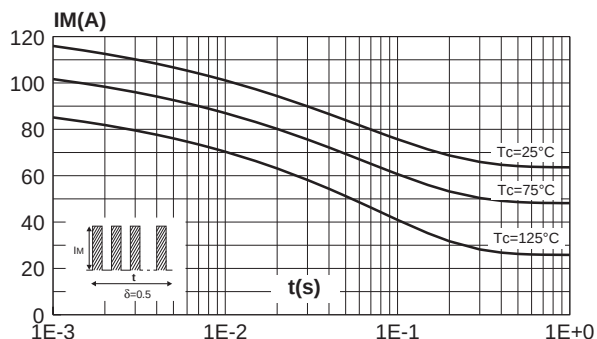


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

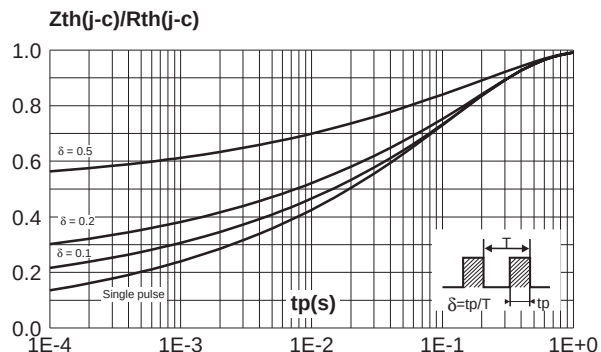


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values) (per diode).

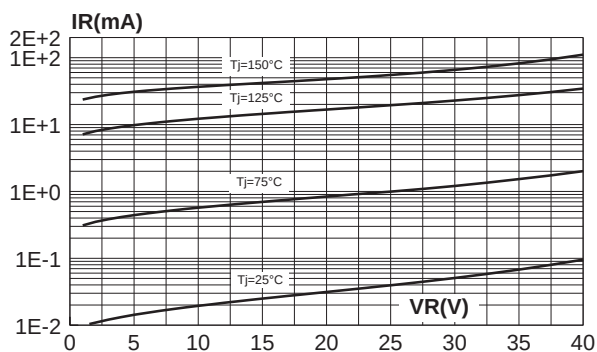


Fig. 8: Junction capacitance versus reverse voltage applied (typical values) (per diode).

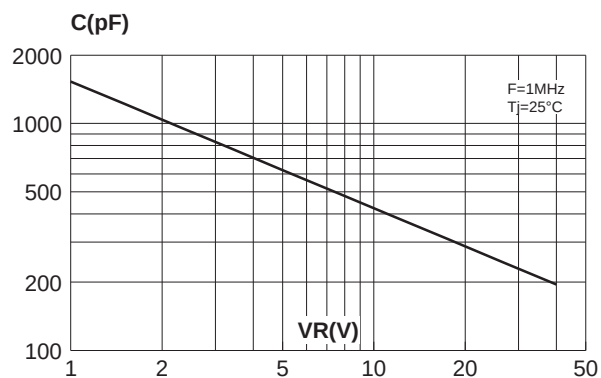
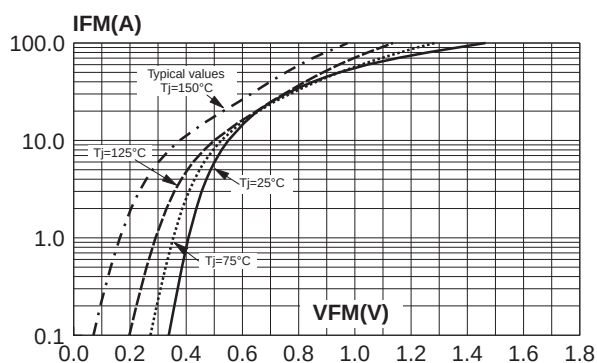


Fig. 9: Forward voltage drop versus forward current (maximum values) (per diode).



STPS16L40CT

PACKAGE MECHANICAL DATA

TO-220AB

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS16L40CT	STPS16L40CT	TO-220AB	2g	50	Tube

- EPOXY MEETS UL94,V0
- COOLING METHOD : C
- RECOMMENDED TORQUE VALUE : 0.55 M.N
- MAXIMUM TORQUE VALUE : 0.70 M.N

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